

3.3V, PCI Express® 3.0, 1-Lane, 2-Channel, 8Gbps, 2:1 Mux/DeMux Switch w/ Single Enable

Features

→ 2 Differential Channel, 2:1 Mux/DeMux

→ PCI Express[®] 3.0 performance, 8.0Gbps

→ Bi-directional operation

→ 3dB Bandwidth: 8.1GHz

→ Low Bit-to-Bit Skew, 10ps max

→ Low channel-to-channel skew: 20ps max

→ Low insertion loss: -1.7dB @4GHz (8.0Gbps)

→ Low return loss: -13.5dB @4GHz (8.0Gbps)

→ Low Crosstalk: -32dB@4GHz (8.0Gbps)

→ Low Off Isolation: -21dB@4GHz (8.0Gbps)

→ Supply Voltage: 3.3V ± 10%

→ Industrial Temperature Range: -40°C to 85°C

→ Low Current: 0.2mA typ.

→ Packaging (Pb-free & Green):

□ - 20-contact TQFN (2.5 × 4.5mm)

□ - 18 contact, X2QFN(XUA18), 2x2mm

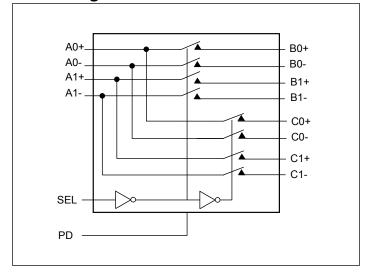
Description

The PI3PCIE3212 is a PCIe Gen3.0, 8Gbps, 4 to 2 differential, bi-directional channel multiplexer/demultiplexer switch. Due to its low bit-to-bit skew, high channel-to-channel noise isolation and bandwidth, this product is ideal for PCI Express* 3.0 signal switching at 8.0Gbps.

Applications

Switch a PCI Express 3.0 lane output between two PCI Express lane inputs. Applications include NBs, PCs, servers, and other embedded devices. Routing of PCI Express 3.0, DP1.2, USB3.0, SAS2.0, SATA3.0, XAUI, RXAUI signals with low signal attenuation.

Block Diagram



Truth Table

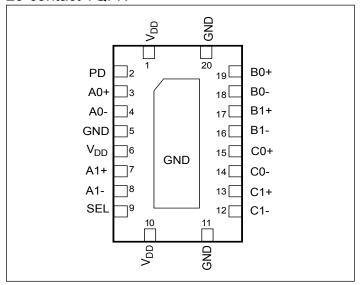
Function	SEL	PD
A to B	L	L
A to C	Н	L
All ports Hi-Z, IC Power Down	X	Н



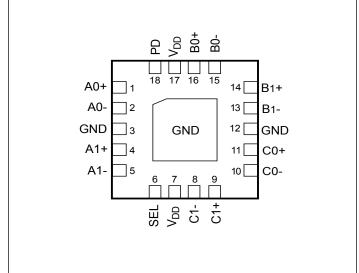


Pin Configuration (Top-side view)

20-contact TQFN



18-contact X2QFN



Pin Description

20-TQFN Pin #	18-X2QFN Pin #	Pin Name	I/O	Description
3 4	1 2	A0+ A0-	I/O	Signal I/O, Channel 0, Port A
7 8	4 5	A1+ A1-	I/O	Signal I/O, Channel 1, Port A
19 18	16 15	B0+ B0-	I/O	Signal I/O, Channel 0, Port B
17 16	14 13	B1+ B1-	I/O	Signal I/O, Channel 1, Port B
15 14	11 10	C0+ C0-	I/O	Signal I/O, Channel 0, Port C
13 12	9 8	C1+ C1-	I/O	Signal I/O, Channel 1, Port C
9	6	SEL	I	Operation mode Select (when SEL=0: A→B, when SEL=1: A→C
2	18	PD	I	PD = 1, Power down is enabled. Please see Truth Table.
1, 6, 10	7, 17	V_{DD}	Pwr	3.3V ±10% Positive Supply Voltage
5, 11, 20	3, 12, Center Pad	GND	Pwr	Power ground





Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

Storage Temperature	-65°C to +150°C
Supply Voltage to Ground Potential	0.5V to +4.6V
Channel DC Input Voltage	0.5V to 1.5V
DC Output Current	120mA
Power Dissipation	0.5W
SEL/PD DC Input Voltage	0.5V to 4.6V
Junction Temperature	125°C

Note: Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Electrical Characteristics

Recommended Operating Conditions

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V_{DD}	3.3V Power Supply		3.0	3.3	3.6	V
I_{DD}	Total current from V _{DD} 3.3V supply	$SEL = OV \text{ or } V_{DD}$		0.2	1	mA
I _{DD_PD}	Power down current	PD = 1		20	40	μΑ
V _{I/O} -DIF	Differential Voltage (differential pins)				1.6	V _{ppd}
V _{I/O-CM}	Common Mode Voltage (differential pins)		0		0.8	V
T _A	Operating temperature range		-40		85	°C

DC Electrical Characteristics for Switching over Operating Range

Parameters	Description	Test Conditions ⁽¹⁾	Min.	Typ.(1)	Max.	Units
V _{IH} - SEL, PD	Input HIGH Voltage, SEL, PD Input		2		3.6	
V _{IL} - _{SEL} , PD	Input LOW Voltage, SEL, PD Input		0		0.8	V
v_{IK}	Clamp Diode Voltage	$V_{DD} = Max., I_{IN} = -18mA$		-0.7	-1.2	
IIH	Input HIGH Current, SEL, PD	$V_{DD} = Max., V_{IN} = V_{DD}$			±5	
IIL	Input LOW Current, SEL, PD	$V_{\mathrm{DD}} = \mathrm{Max.}, V_{\mathrm{IN}} = 0\mathrm{V}$			±5	μΑ
IIH	Input HIGH Current, A _X , B _X , C _X	$V_{\mathrm{DD}} = \mathrm{Max.}, V_{\mathrm{IN}} = 1.5\mathrm{V}$	-10		+10	
IIL	Input LOW Current, A _X , B _X , C _X	$V_{\mathrm{DD}} = \mathrm{Max.}, V_{\mathrm{IN}} = 0\mathrm{V}$	-10		+10	μΑ
IOZH	HighZ HIGH Current, B _X , C _X	$V_{\rm DD}$ = Max., $V_{\rm IN}$ = 1.5V	-10		+10	μΑ
IOZL	HighZ LOW Current, BX, CX	$V_{\rm DD} = Max., V_{\rm IN} = 0V$	-10		+10	μΑ

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Note:

^{1.} Typical values are at $V_{DD} = 3.3V$, $T_A = 25$ °C ambient and maximum loading.





Switching Characteristics

Parameters	Description	Test Conditions	Min.	Тур.	Max.	Units
tpZH, tpZL	Line Enable Time - SEL to A _N , B _N , C _N			25	30	
t _{PHZ} , t _{PLZ}	Line Disable Time - SEL to A _N , B _N , C _N			5	25	ns
$t_{\rm PLH}$	Propagation Delay, LOW to HIGH		17		36	ps
t_{PHL}	Propagation Delay, HIGH to LOW		21		39	ps
t _{b-b}	Bit-to-bit skew within the same differential pair			5	10	ps
t _{ch-ch}	Channel-to-channel skew		_		20	ps

Dynamic Electrical Characteristics

Parameter	Description	Test Conditions	Min.	Typ. ¹	Max.	Units
		f = 100MHz		-0.4		
	D:0 1	f = 100MHz-1.25GHz		-0.6		
DDIL ^{2, 3}	Differential Insertion Loss	f = 1.25GHz-2.5GHz		-1.0		dB
	$(V_{IN} = -10dBm, DC = 0V)$	f = 2.5GHz-4GHz		-1.7		
		f = 5GHz		-2.1		
DDIL _{OFF} ^{2, 3}		f = 100MHz		-59		
	Differential Off Isolation	f = 100MHz-1.25GHz		-37		10
		f = 1.25GHz-2.5GHz		-27		dB
		f = 2.5GHz-4GHz		-21		
	Differential Return Loss	f = 100MHz		-27		
DDRL ²		f = 100MHz-1.25GHz		-23.3		dr.
DDKL		f = 1.25GHz-2.5GHz		-23.3		dB
		f = 2.5GHz-4GHz		-13.5		
DDNEXT ^{2, 3}	Near End Crosstalk	f = 100MHz		-57		
		f = 100MHz-1.25GHz		-38		JD.
		f = 1.25GHz-2.5GHz		-33		dB
		f = 2.5GHz-4GHz		-32		
BW	-3dB Bandwidth			8.1		GHz

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Notes:

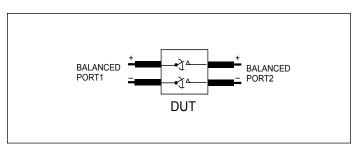
^{1.} Guaranteed by design. Typical values are at V_{DD} = 3.3V , T_A = 25°C ambient and maximum loading.

^{2.} S parameters are measured with our evaluation board made with Rogers (R04350) material. Trace width is 30 mil, length 540 mil, trace impedance is 50 Ohm (+/-5%) and total insertion loss of the trace is 0.5dB@4GHz.

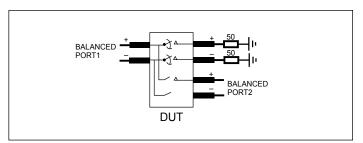
^{3.} Measurement done with fixture deembedding.



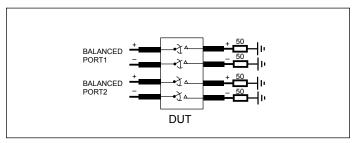




Diff. Insertion Loss and Return Test Circuit

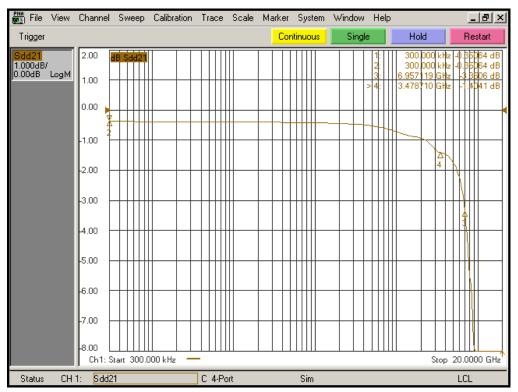


Diff. Off Isolation Test Circuit



Diff. Near End Xtalk Test Circuit



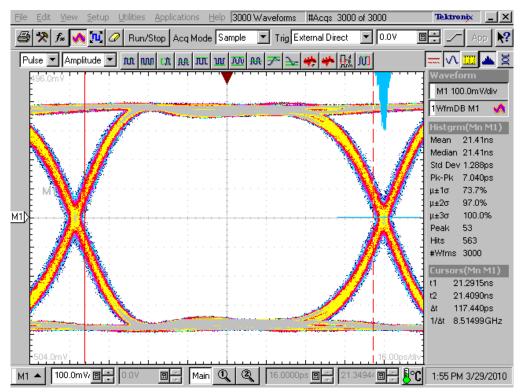


Differential Insertion Loss

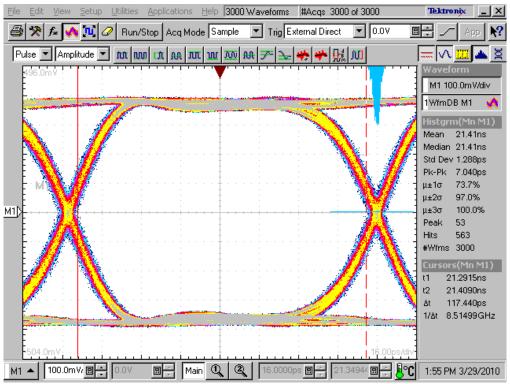


Differential Return Loss



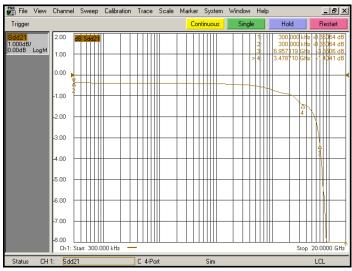


Differential Off Isolation

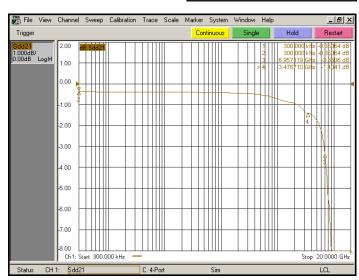


Differential Crosstalk

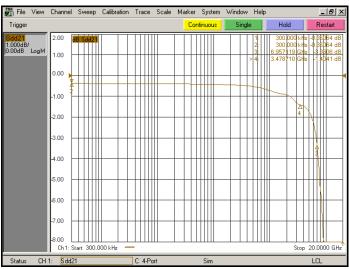




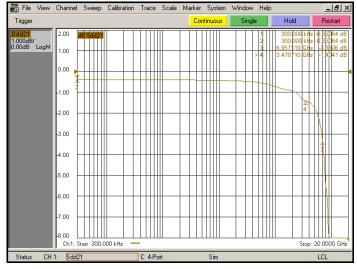
5.0 Gbps RX signal eye without PI3PCIE3212



5.0 Gbps RX signal eye with PI3PCIE3212



8.0 Gbps RX signal eye without PI3PCIE3212

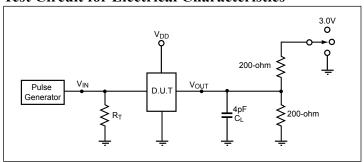


8.0 Gbps RX signal eye with PI3PCIE3212





Test Circuit for Electrical Characteristics(1-5)



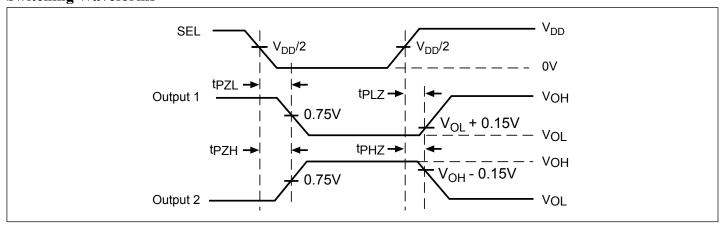
Notes:

- 1. $C_L = Load$ capacitance: includes jig and probe capacitance.
- 2. R_T = Termination resistance: should be equal to Z_{OUT} of the Pulse Generator
- 3. Output 1 is for an output with internal conditions such that the output is low except when disabled by the output control. output 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- 4. All input impulses are supplied by generators having the following characteristics: $PRR \le MHz$, $Z_O = 50\Omega$, $t_R \le 2.5$ ns, $t_F \le 2.5$ ns.
- 5. The outputs are measured one at a time with one transition per measurement.

Switch Positions

Test	Switch
t _{PLZ} , t _{PZL}	3.0V
t _{PHZ} , t _{PZH}	GND

Switching Waveforms

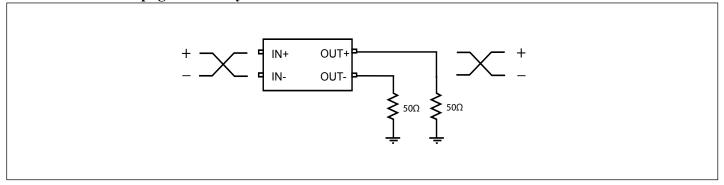


Voltage Waveforms Enable and Disable Times

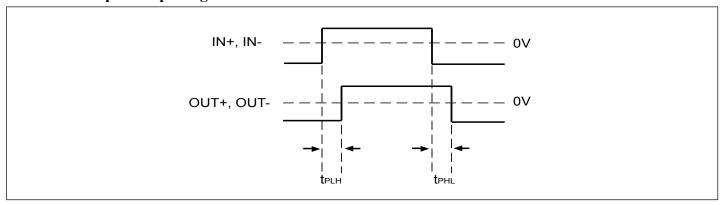




Test Circuit for Propagation Delay



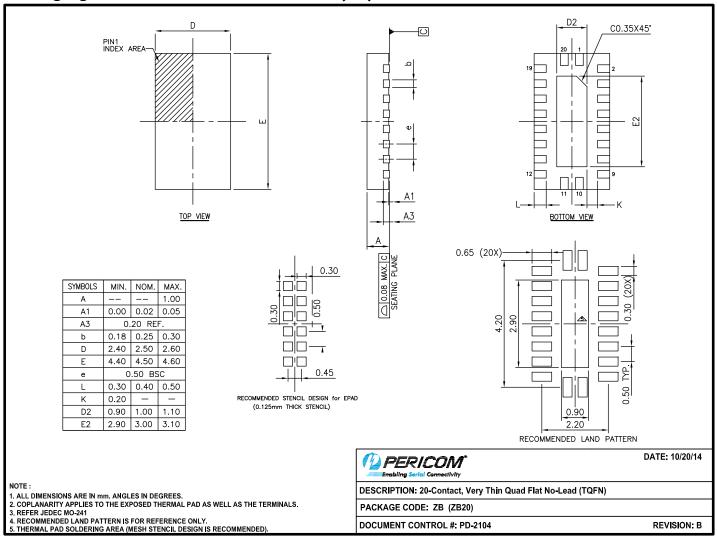
Differential Input/Output Signal Waveform







Packaging Mechanical: 20-Contact TQFN (ZB)



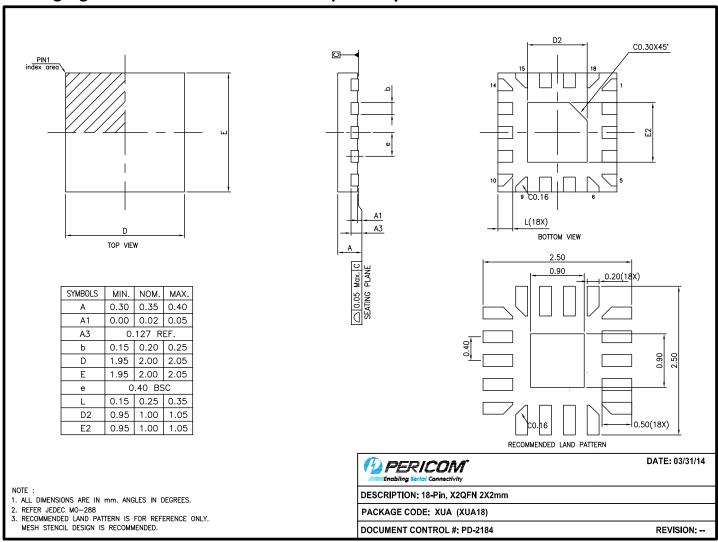
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14-0265





Packaging Mechanical: 18-Contact XUA (X2QFN)



14-0039

For latest package info.

 $please\ check: http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/pericom-packaging-mechanicals-and-thermal-characteristics/pericom-packaging-packaging-mechanicals-and-thermal-characteristics/pericom-packaging-packaging-mechanicals-and-thermal-characteristics/pericom-packaging-packaging-mechanicals-and-thermal-characteristics/pericom-packaging-packaging-mechanicals-and-thermal-characteristics/pericom-packaging-packagin$

Ordering Information

Ordering Code	Package Code	Package Type
PI3PCIE3212ZBEX	ZB	20-contact, Very Thin Quad Flat No-Lead (TQFN), Tape & Reel
PI3PCIE3212XUAEX	XUA	18-Pin, 2x2mm (X2QFN), Tape & Reel

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Notes:

- Thermal characteristics can be found on the company web site at www.diodes.com/design/support/packaging/
- E = Pb-free and Green
- Adding an X suffix = Tape/Reel





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